

Claim 7, line 3, change ";" to --,--; and

line 7, change "but" to --, but--.

Q3
8. (Amended) A process for producing a barrier film for forming a barrier film made of a thin film of the nitride of a high temperature-melting point metal on a substrate, [wherein;] comprising the steps of:

exposing the surface of said substrate [is exposed] to a plasma of hydrogen gas and a plasma containing at least one gas selected from [among] the group consisting of argon, nitrogen and helium gases[,]; and [then]

forming the thin film of the nitride of said high temperature-melting point metal [is formed] on the surface of the substrate.

Claim 9, line 2, delete ";".

Claim 10, line 5, delete ";".

REMARKS

The above amendments are believed to place the application in proper condition for examination. Early and favorable action is awaited.

In the event there are any additional fees required, please charge our Deposit
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Respectfully submitted,

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Enclosure: Substitute Abstract of the Disclosure